

MMBTA20

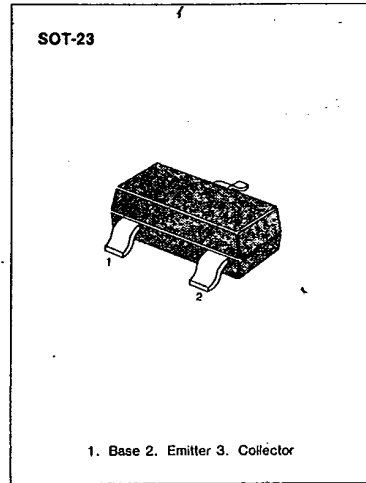
NPN EPITAXIAL SILICON TRANSISTOR

GENERAL PURPOSE TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	4	V
Collector Current	I _C	100	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C

• Refer to MMBT3904 for graphs



ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C = 1.0mA, I _B = 0	40		V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = 100μA, I _C = 0	4		V
Collector Cutoff Current	I _{CEO}	V _{CB} = 30V, I _E = 0		100	nA
DC Current Gain	h _{FE}	V _{CE} = 10V, I _C = 5mA	40	400	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 10mA, I _B = 1.0mA		0.25	V
Current Gain-Bandwidth Product	f _T	I _C = 5.0mA, V _{CE} = 10V f = 100MHz	125		MHz
Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0 f = 100KHz		4	pF

Marking

